

MJ P-Channel Enhancement Mode Power MOSFET

Description

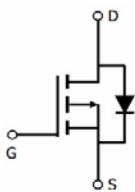
The MJ20P05Y uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

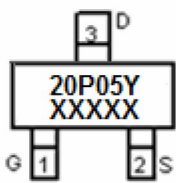
- ◆ $V_{DS} = -20V, I_D = -5A$
 $R_{DS(ON)} < 25m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 40m\Omega @ V_{GS} = -2.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Application

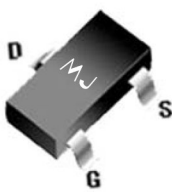
- ◆ Motor drive
- ◆ Load switch
- ◆ Power management



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
20P05Y	MJ20P05Y	SOT23-3L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_c =25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-5	A
Pulsed Drain Current ^(Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	83.3	°C/W
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Electrical Characteristics (T_A =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	-0.5	-0.7	-1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-5A	-	20	25	mΩ
		V _{GS} =-2.5V, I _D =-5A	-	30	40	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-5A	-	17	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	620	-	PF
Output Capacitance	C _{OSS}		-	125	-	PF
Reverse Transfer Capacitance	C _{rss}		-	64	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, ,R _L =10Ω V _{GS} =-4.5V,R _{GEN} =6Ω	-	4.5	-	nS
Turn-on Rise Time	t _r		-	9.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	18.7	-	nS
Turn-Off Fall Time	t _f		-	3.3	-	nS
Total Gate Charge	Q _g	V _{DS} =-10V,I _D =-5A, V _{GS} =-4.5V	-	15	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =-5A	-		-1.2	V

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

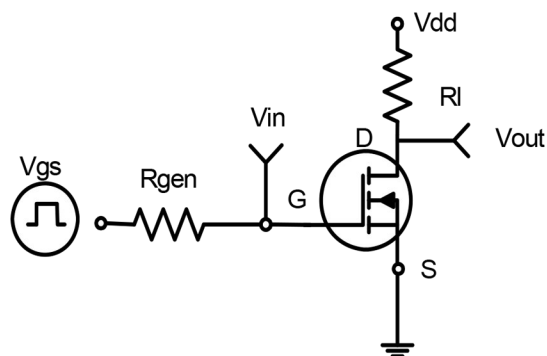


Figure 1 Switching Test Circuit

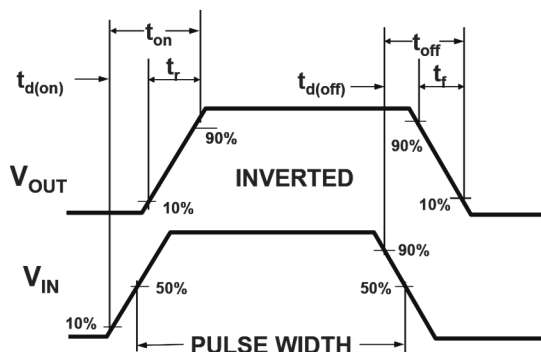


Figure 2 Switching Waveforms

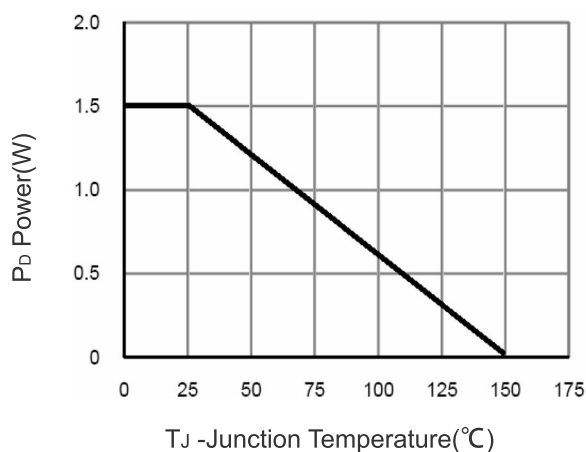


Figure 3 Power Dissipation

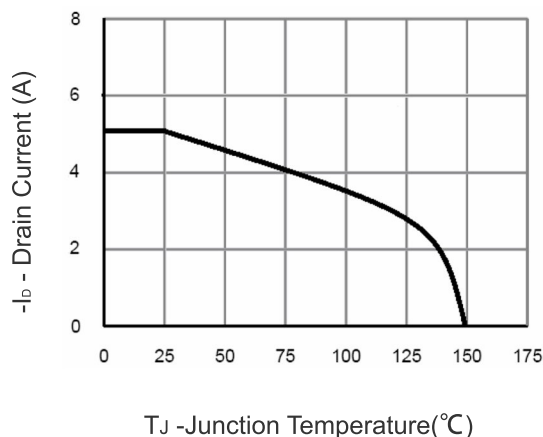


Figure 4 Drain Current

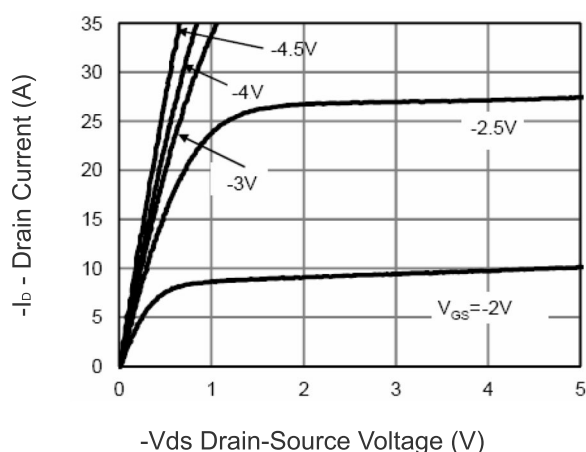


Figure 5 Output Characteristics

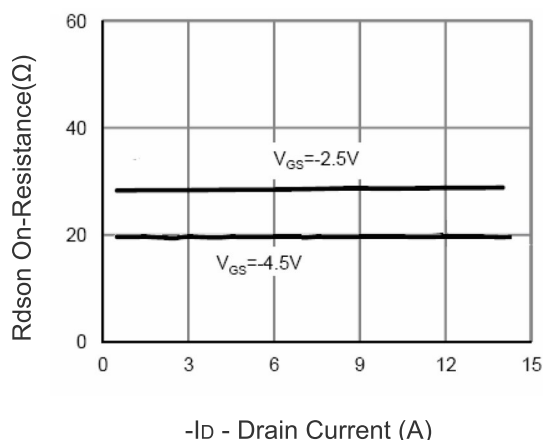


Figure 6 Drain-Source On-Resistance

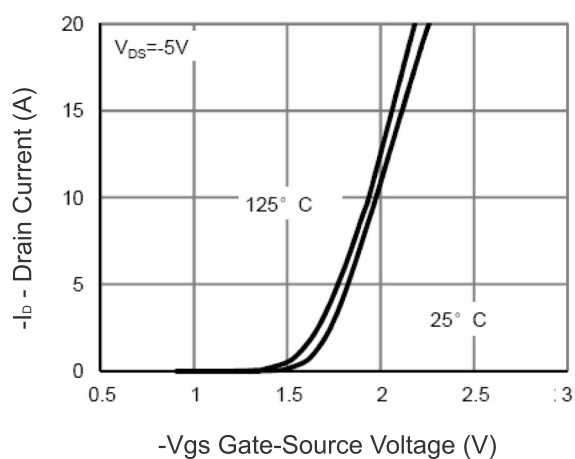


Figure 7 Transfer Characteristics

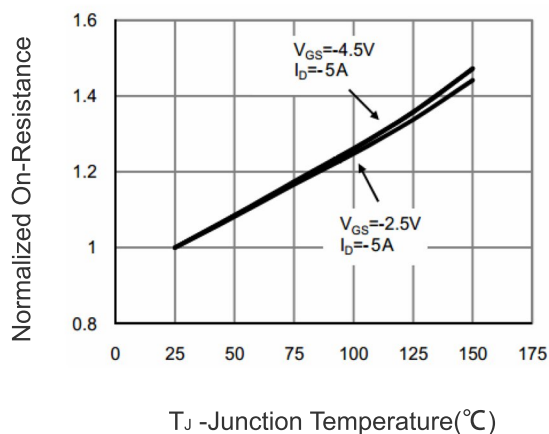


Figure 8 Drain-Source On-Resistance

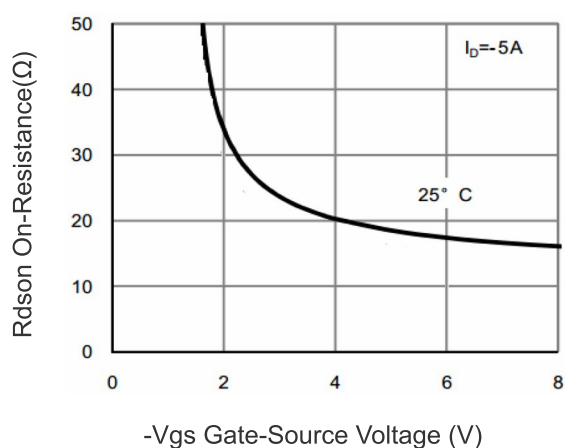


Figure 9 Rdson vs Vgs

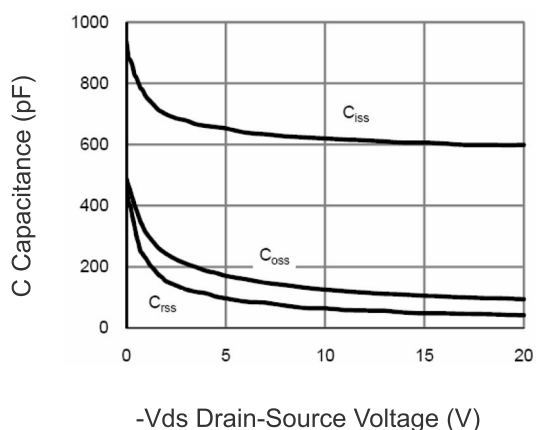


Figure 10 Capacitance vs Vds

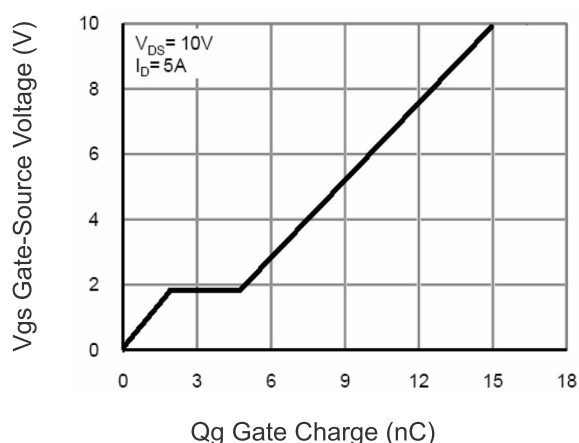


Figure 11 Gate Charge

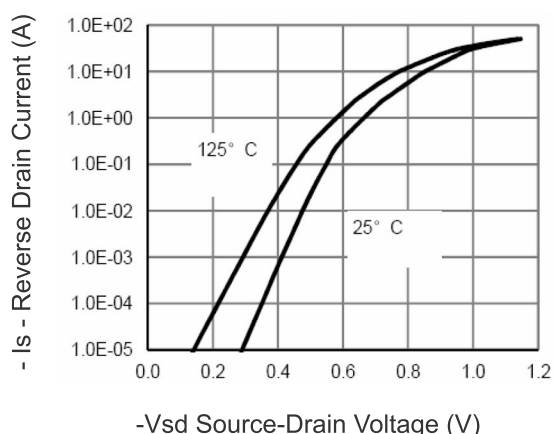
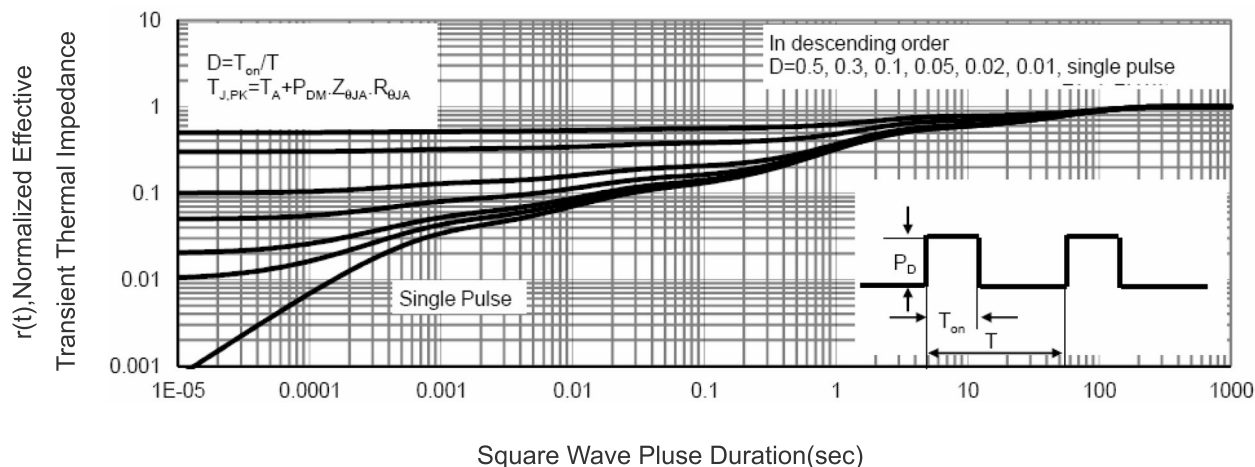
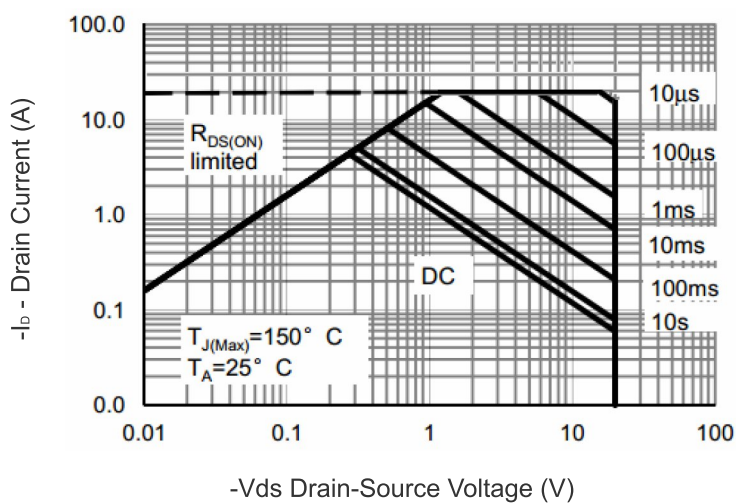
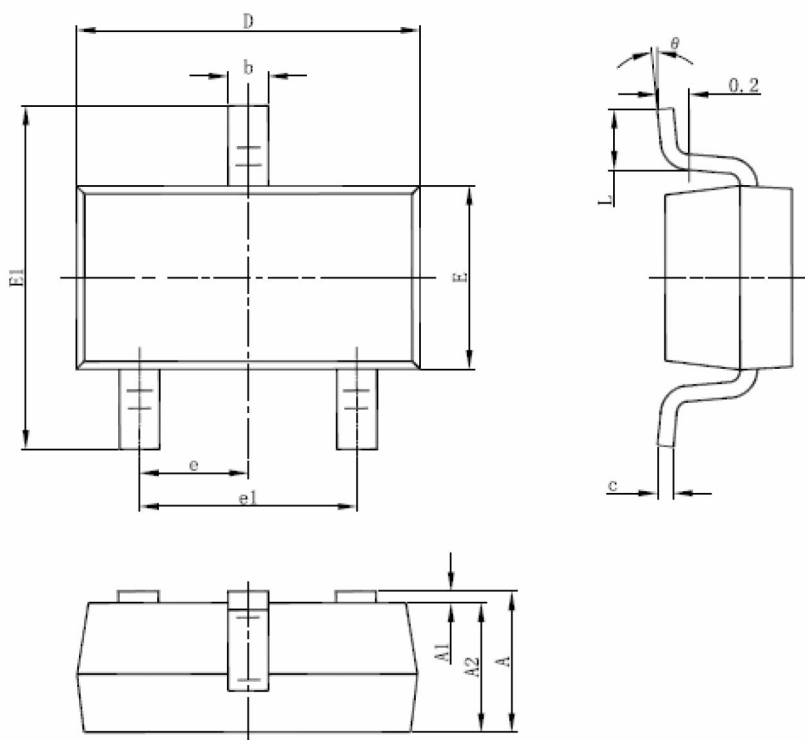


Figure 12 Source- Drain Diode Forward



SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

- Notes:**
- ① All dimensions are in millimeters.
 - ② Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
 - ③ Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
 - ④ Dimension L is measured in gauge plane.
 - ⑤ Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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